

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (L<sup>2</sup>-π-MOS V)

# 2SJ360

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- 4V GATE DRIVE
- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 0.55\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 0.9S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = -100\mu A$  (Max.) ( $V_{DS} = -60V$ )
- Enhancement-Mode :  $V_{th} = -0.8 \sim -2.0V$   
( $V_{DS} = -10V, I_D = -1mA$ )

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		$V_{DS}$	-60	V
Drain-Gate Voltage ( $R_{GS} = 20k\Omega$ )		$V_{DGR}$	-60	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Drain Current	DC	$I_D$	-1	A
	Pulse	$I_{DP}$	-3	A
Drain Power Dissipation (Ta = 25°C)		$P_D$	0.5	W
Drain Power Dissipation*		$P_D$	1.5	W
Channel Temperature		$T_{ch}$	150	°C
Storage Temperature Range		$T_{stg}$	-55~150	°C

\* : Mounted on ceramic substrate (1inch<sup>2</sup> × 0.8t)

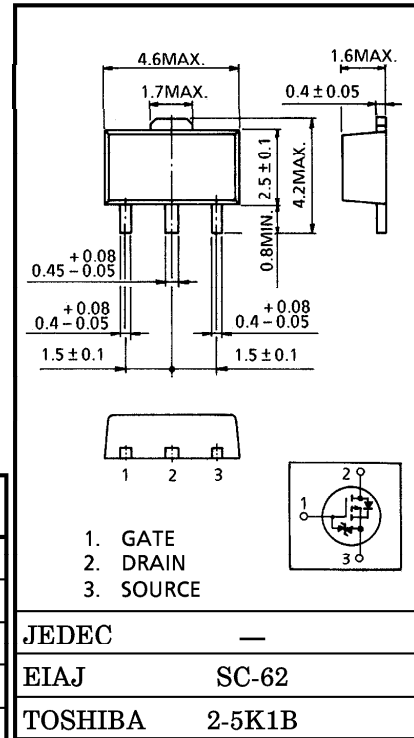
THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel To Ambient	$R_{th(ch-a)}$	250	°C/W

**This transistor is an electrostatic sensitive device.  
Please handle with caution.**

INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 0.05g (Typ.)

MARKING



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**ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	$\pm 10$	$\mu A$
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = -60V, V_{GS} = 0V$	—	—	100	$\mu A$
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = -10mA, V_{GS} = 0V$	-60	—	—	V
Gate Threshold Voltage		$V_{th}$	$V_{DS} = -10V, I_D = -1mA$	-0.8	—	-2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = -4V, I_D = -0.5A$	—	0.86	1.2	$\Omega$
			$V_{GS} = -10V, I_D = -0.5A$	—	0.55	0.73	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10V, I_D = -0.5A$	0.5	0.9	—	S
Input Capacitance		$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0V$ $f = 1MHz$	—	155	—	pF
Reverse Transfer Capacitance		$C_{rss}$		—	20	—	
Output Capacitance		$C_{oss}$		—	75	—	
Switching Time	Rise Time	$t_r$		—	17	—	ns
	Turn-on Time	$t_{on}$		—	20	—	
	Fall Time	$t_f$		—	20	—	
	Turn-off Time	$t_{off}$		$V_{IN} : t_r, t_f < 5ns$ $Duty \leq 1\%, t_w = 10\mu s$	—	100	
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} = -48V, V_{GS} = -10V$ $I_D = -1A$	—	6.5	—	nC
Gate-Source Charge		$Q_{gs}$		—	4.5	—	
Gate-Drain (“Miller”) Charge		$Q_{gd}$		—	2.0	—	

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)**

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	-1	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	-3	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = -1A, V_{GS} = 0V$	—	—	1.7	V
Reverse Recovery Time	$t_{rr}$	$I_{DR} = -1A, V_{GS} = 0V$	—	50	—	ns
Reverse Recovery Charge	$Q_{rr}$	$dI_{DR} / dt = 50A / \mu s$	—	50	—	$\mu C$

